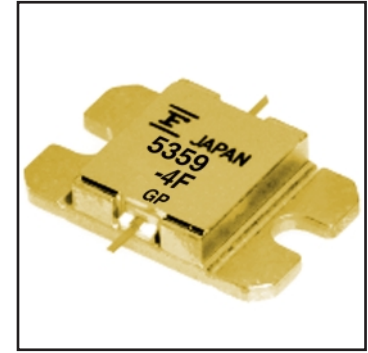


### FEATURES

- High Output Power:  $P_{1dB} = 36.5\text{dBm}$  (Typ.)
- High Gain:  $G_{1dB} = 10.5\text{dB}$  (Typ.)
- High PAE:  $\eta_{add} = 37\%$  (Typ.)
- Low  $IM_3 = -46\text{dBc}$ @ $P_o = 25.5\text{dBm}$
- Broad Band: 5.3 ~ 5.9GHz
- Impedance Matched  $Z_{in}/Z_{out} = 50\Omega$
- Hermetically Sealed Package



### DESCRIPTION

The FLM5359-4F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

### ABSOLUTE MAXIMUM RATING (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_c = 25^\circ\text{C}$	25.0	W
Storage Temperature	$T_{stg}$		-65 to +175	$^\circ\text{C}$
Channel Temperature	$T_{ch}$		175	$^\circ\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.2 mA respectively with gate resistance of  $100\Omega$ .

### ELECTRICAL CHARACTERISTICS (Ambient Temperature $T_a=25^\circ\text{C}$ )

Item	Symbol	Test Conditions	Limit			Unit	
			Min.	Typ.	Max.		
Saturated Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	1950	2900	mA	
Transconductance	$g_m$	$V_{DS} = 5\text{V}, I_{DS} = 1100\text{mA}$	-	1000	-	mS	
Pinch-off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 90\text{mA}$	-1.0	-2.0	-3.5	V	
Gate Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -90\mu\text{A}$	-5.0	-	-	V	
Output Power at 1dB G.C.P.	$P_{1dB}$	$V_{DS} = 10\text{V},$ $I_{DS} = 0.55 I_{DSS}$ (Typ.), $f = 5.3 \sim 5.9\text{GHz},$ $Z_S = Z_L = 50\text{ohm}$	35.5	36.5	-	dBm	
Power Gain at 1dB G.C.P.	$G_{1dB}$		9.5	10.5	-	dB	
Drain Current	$I_{dsr}$		-	1100	1300	mA	
Power-added Efficiency	$\eta_{add}$		-	37	-	%	
Gain Flatness	$\Delta G$		-	-	$\pm 0.6$	dB	
3rd Order Intermodulation Distortion	$IM_3$		$f = 5.9\text{GHz}, \Delta f = 10\text{MHz}$ 2-Tone Test $P_{out} = 25.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	$R_{th}$		Channel to Case	-	5.0	6.0	$^\circ\text{C}/\text{W}$
Channel Temperature Rise	$\Delta T_{ch}$	$10\text{V} \times I_{dsr} \times R_{th}$	-	-	80	$^\circ\text{C}$	

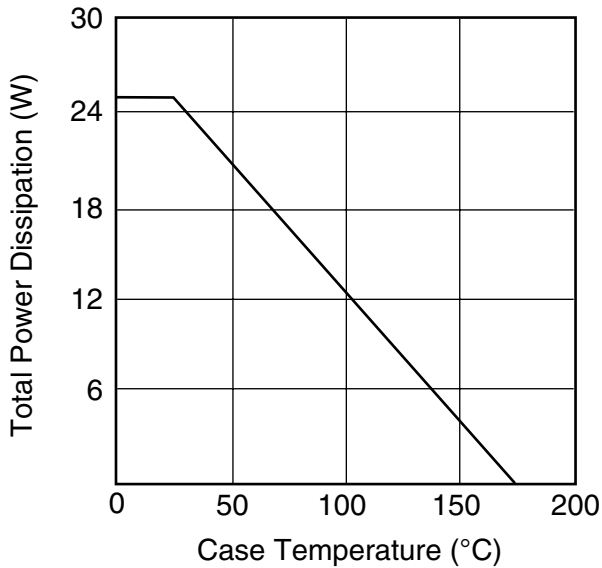
CASE STYLE: IB

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

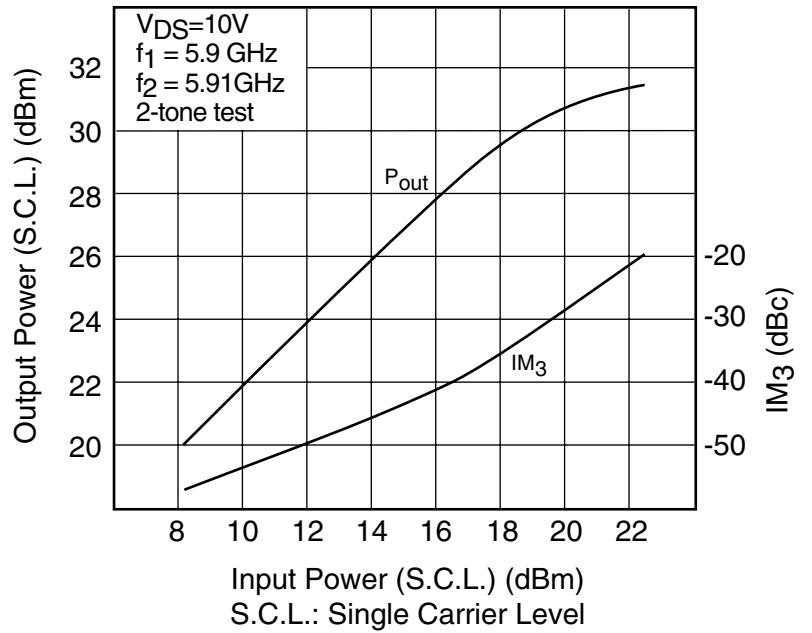
# FLM5359-4F

## C-Band Internally Matched FET

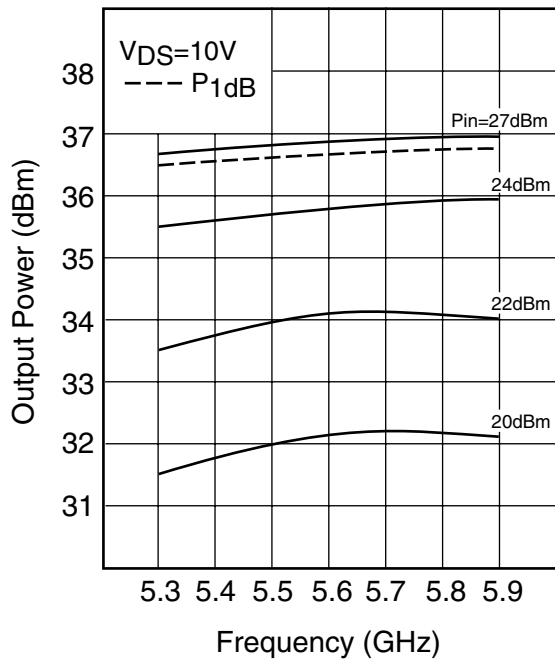
**POWER DERATING CURVE**



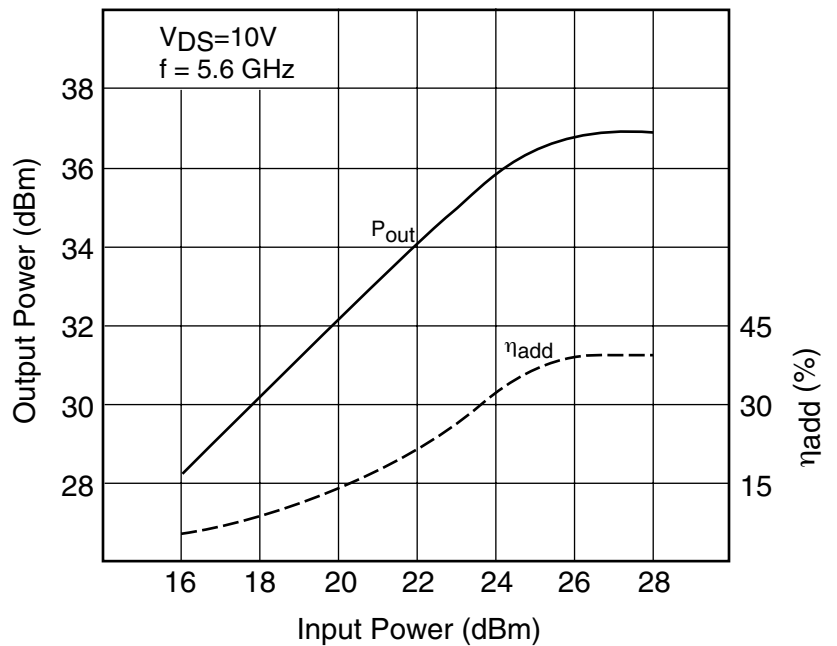
**OUTPUT POWER & IM<sub>3</sub> vs. INPUT POWER**

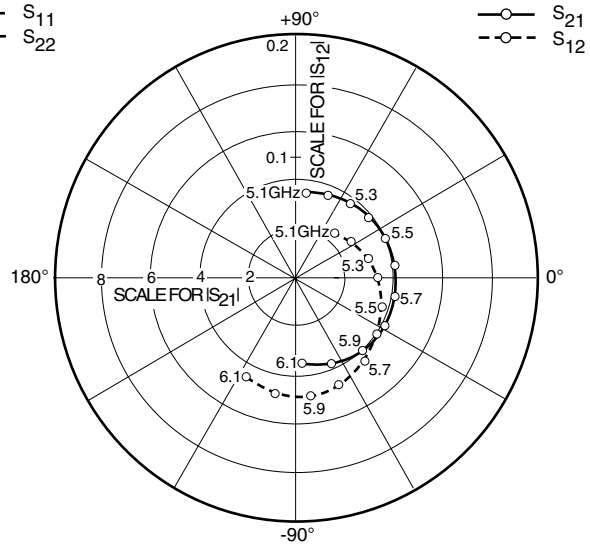
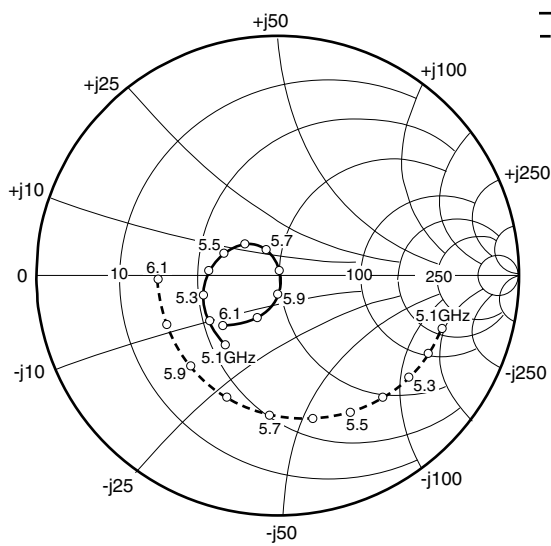


**OUTPUT POWER vs. FREQUENCY**



**OUTPUT POWER vs. INPUT POWER**





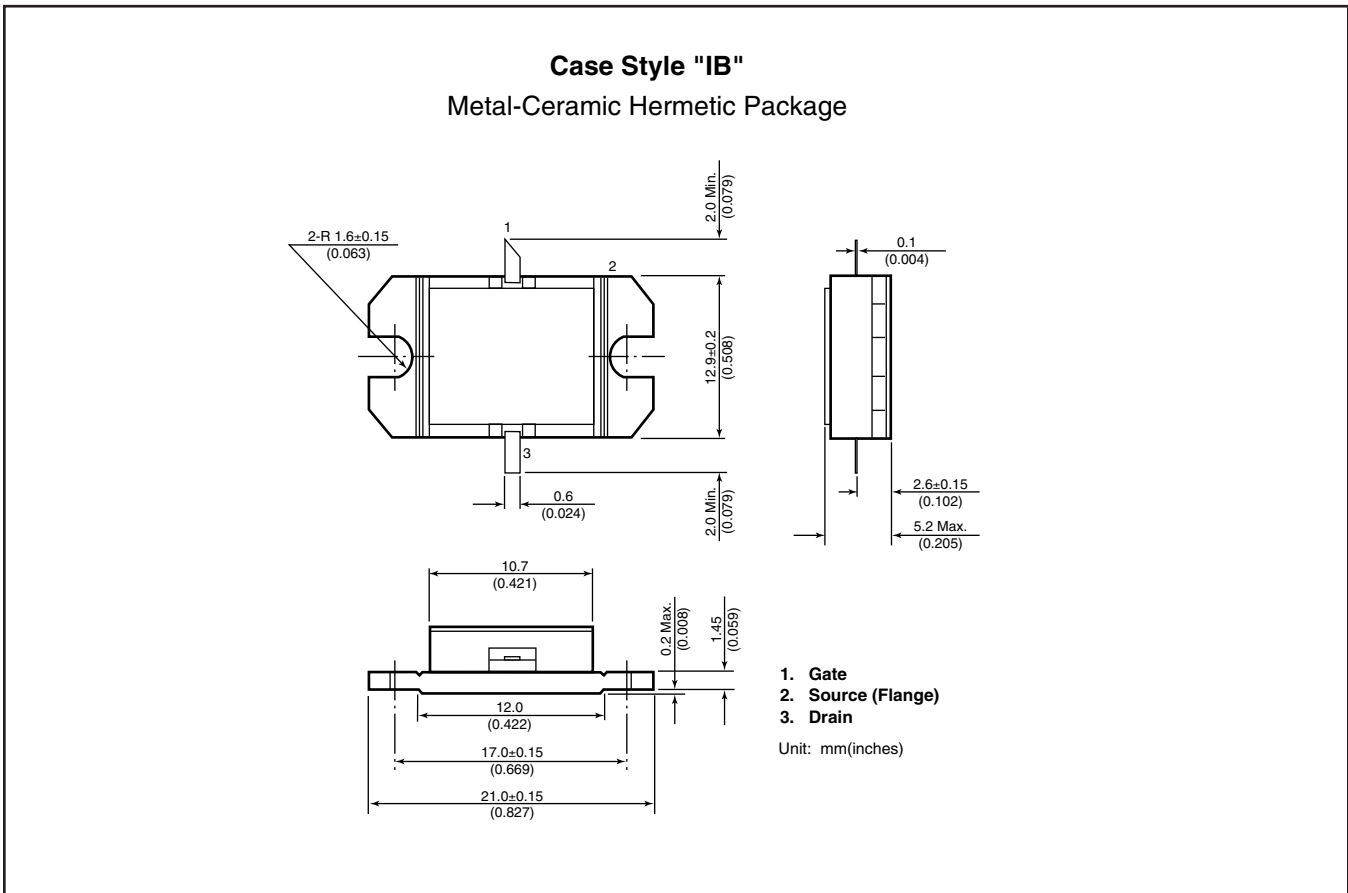
### S-PARAMETERS

$V_{DS} = 10V, I_{DS} = 1100mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5100	.363	-126.5	3.558	83.3	.048	48.4	.708	-18.0
5200	.341	-146.1	3.665	69.1	.054	31.8	.697	-27.6
5300	.317	-165.4	3.769	54.5	.062	14.5	.680	-38.0
5400	.287	175.9	3.887	39.5	.068	-0.5	.664	-49.3
5500	.244	156.5	4.001	23.8	.076	-17.8	.642	-62.2
5600	.189	136.3	4.092	7.2	.083	-33.6	.611	-76.7
5700	.116	113.0	4.150	-10.5	.089	-49.8	.579	-93.9
5800	.029	69.0	4.141	-29.0	.093	-67.8	.548	-113.2
5900	.082	-88.4	4.025	-48.1	.097	-83.5	.524	-134.1
6000	.195	-115.1	3.822	-67.5	.096	-100.3	.508	-156.3
6100	.309	-137.5	3.523	-86.8	.091	-117.0	.502	-178.2

# FLM5359-4F

## C-Band Internally Matched FET



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### CAUTION

Fujitsu Compound Semiconductor Products contain **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.